Abstracts

A Study of High Power Pulsed Characteristics of Low-Noise GaAs MESFET's (Dec. 1981 [T-MTT])

D.S. James and L. Dormer. "A Study of High Power Pulsed Characteristics of Low-Noise GaAs MESFET's (Dec. 1981 [T-MTT])." 1981 Transactions on Microwave Theory and Techniques 29.12 (Dec. 1981 [T-MTT] (1981 Symposium Issue)): 1298-1310.

Low-noise GaAs MESFET’s of various types have been investigated for short-term catastrophic burnout ratings when exposed to pulses from an X -band radar transmitter 6 = T/R cell combination. Failure modes have been categorized, and SEM, EDAX and optical techniques employed in the associated failure analyses. A limited number of longer term tests at lower pulse levels are also described. Post-dosage, interpulse RF performance has been studied by use of a special test set described, the initial results obtained are presented.

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